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cont'd

a second cladding layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer,

wherein an $\text{In}_x\text{Ga}_{1-x}\text{N}$ layer of the first conductivity type is formed between the substrate and the first cladding layer, and $x \geq y$ in the composition of In.

2. (Amended) The device of claim 1, wherein the $\text{In}_x\text{Ga}_{1-x}\text{N}$ layer is formed in contact with the first cladding layer

3. (Amended) The device of Claim 1, wherein the $\text{In}_x\text{Ga}_{1-x}\text{N}$ layer is formed in contact with the substrate.

A1
cont'd

4. (Amended) A semiconductor laser device comprising:
a first cladding layer, which is made of a nitride semiconductor of a first conductivity type and is formed over a substrate;

an active layer, which is made of $\text{In}_y\text{Ga}_{1-y}\text{N}$ and is formed over the first cladding layer;

a second cladding layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer; and

an electrode formed over the second cladding layer,

wherein an $\text{In}_x\text{Ga}_{1-x}\text{N}$ layer of the second conductivity type is formed between the second cladding layer and the electrode, and $x \geq y$ in the composition of In.

5. (Amended) The device of Claim 4, wherein the $\text{In}_x\text{Ga}_{1-x}\text{N}$ layer is formed in contact with the second cladding layer.

6. (Amended) The device of Claim 4, wherein the $\text{In}_x\text{Ga}_{1-x}\text{N}$ layer is formed in contact with the electrode.